# RENESAS BCR3PM-14LG

Triac Medium Power Use

| REJ03G1557-0100 |  |  |  |  |  |
|-----------------|--|--|--|--|--|
| Rev.1.00        |  |  |  |  |  |
| Jul 06, 2007    |  |  |  |  |  |

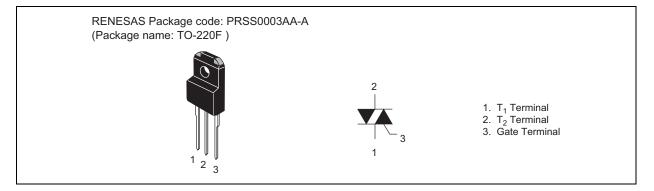
### Features

- $I_{T(RMS)}: 3 A$
- $V_{DRM}$  : 800 V (Tj = 125°C)
- $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGTII}$  : 30 mA
- Viso : 2000 V

- The Product guaranteed maximum junction temperature 150°C
- Insulated Type
- Planar Type
- UL Recognized: Yellow Card No. E223904

File No. E80271

# Outline



### Applications

Washing machine, inversion operation of capacitor motor, and other general controlling devices

### **Maximum Ratings**

| Parameter  | Symbol           | Voltage class | Unit | Conditions |
|--|------------------|---------------|------|------------|
| Falalletei   | Symbol           | 14            | Onic |            |
| Repetitive peak off-state voltage <sup>Note1</sup>     | V <sub>DRM</sub> | 800           | V    | Tj = 125°C |
|  |                  | 700           | V    | Tj = 150°C |
| Non-repetitive peak off-state voltage <sup>Note1</sup> | V <sub>DSM</sub> | 840           | V    |            |

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| Parameter                      | Symbol               | Ratings      | Unit             | Conditions  |
|--------------------------------|----------------------|--------------|------------------|---|
| RMS on-state current           | I <sub>T (RMS)</sub> | 3.0          | A                | Commercial frequency, sine full wave 360° conduction, Tc = 130°C                |
| Surge on-state current         | I <sub>TSM</sub>     | 30           | A                | 60Hz sinewave 1 full cycle, peak value, non-repetitive                          |
| I <sup>2</sup> t for fusing    | l <sup>2</sup> t     | 3.7          | A <sup>2</sup> s | Value corresponding to 1 cycle of half wave 60Hz, surge on-state current        |
| Peak gate power dissipation    | P <sub>GM</sub>      | 5            | W                |   |
| Average gate power dissipation | P <sub>G (AV)</sub>  | 0.5          | W                |   |
| Peak gate voltage              | V <sub>GM</sub>      | 10           | V                |   |
| Peak gate current              | I <sub>GM</sub>      | 2            | А                |   |
| Junction temperature           | Tj                   | - 40 to +150 | °C               |   |
| Storage temperature            | Tstg                 | - 40 to +150 | °C               |   |
| Mass                           | —                    | 2.0          | g                | Typical value   |
| Isolation voltage              | Viso                 | 2000         | V                | Ta = 25°C, AC 1 minute,<br>T <sub>1</sub> • T <sub>2</sub> • G terminal to case |

Notes: 1. Gate open.

# **Electrical Characteristics**

| Parameter   |     | Symbol                | Min.    | Тур. | Max. | Unit | Test conditions  |
|---|-----|-----------------------|---------|------|------|------|--|
| Repetitive peak off-state current   |     | I <sub>DRM</sub>      | —       | —    | 2.0  | mA   | Tj = 150°C, V <sub>DRM</sub> applied                                 |
| On-state voltage  |     | V <sub>TM</sub>       | —       | —    | 1.6  | V    | $Tc = 25^{\circ}C$ , $I_{TM} = 4.5 A$ ,<br>Instantaneous measurement |
| Gate trigger voltage <sup>Note2</sup>                                     | Ι   | $V_{\text{FGT}I}$     | —       | —    | 1.5  | V    | $Tj=25^{\circ}C,V_{D}=6~V,R_{L}=6~\Omega,$                           |
|   | II  | V <sub>RGTI</sub>     | —       | —    | 1.5  | V    | R <sub>G</sub> = 330 Ω   |
|   | III | V <sub>RGTIII</sub>   | _       | —    | 1.5  | V    |  |
| Gate trigger current <sup>Note2</sup>                                     | Ι   | I <sub>FGTI</sub>     | —       | —    | 30   | mA   | $Tj=25^{\circ}C,V_{D}=6~V,R_{L}=6~\Omega,$                           |
|   | II  | I <sub>RGTI</sub>     | _       | —    | 30   | mA   | R <sub>G</sub> = 330 Ω   |
|   | III | I <sub>RGTIII</sub>   | —       | —    | 30   | mA   |  |
| Gate non-trigger voltage  |     | V <sub>GD</sub>       | 0.2/0.1 | —    | —    | V    | $Tj = 125^{\circ}C/150^{\circ}C, V_D = 1/2 V_{DRM}$                  |
| Thermal resistance  |     | R <sub>th (j-c)</sub> | —       | —    | 5.2  | °C/W | Junction to case <sup>Note3</sup>                                    |
| Critical-rate of rise of off-stat<br>commutating voltage <sup>Note4</sup> | e   | (dv/dt)c              | 5/1     |      | —    | V/µs | Tj = 125°C/150°C   |

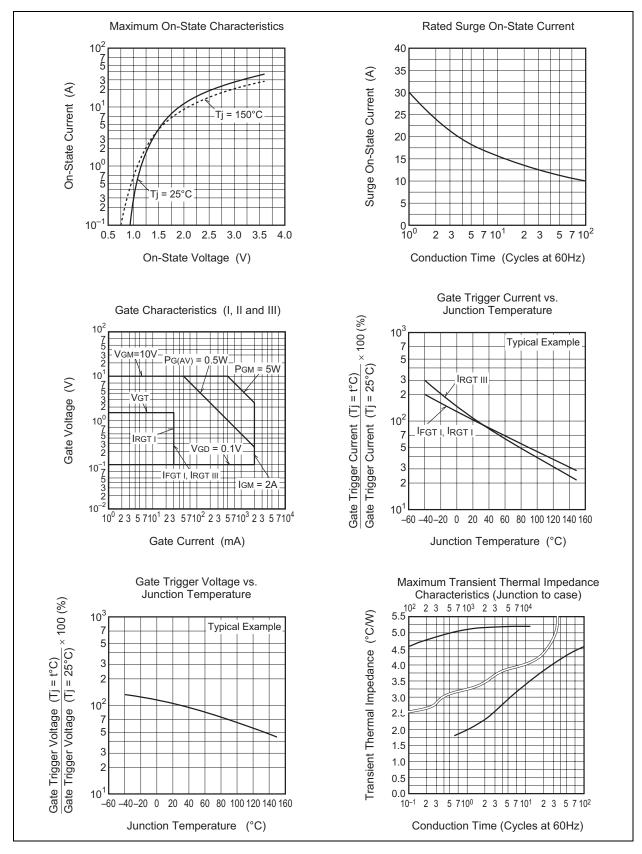
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance  $R_{th \ (c-f)}$  in case of greasing is 0.5°C/W.

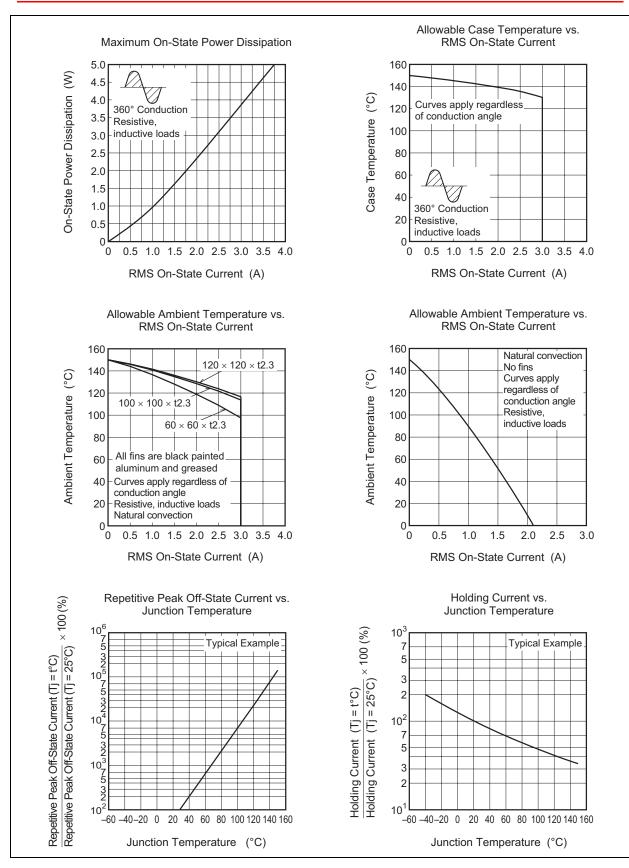
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

| Test conditions  | Commutating voltage and current waveforms<br>(inductive load) |  |  |
|--|---|--|--|
| 1. Junction temperature<br>Tj = 125°C/150°C                              | Supply Voltage → Time   |  |  |
| 2. Rate of decay of on-state commutating current<br>(di/dt)c = -1.5 A/ms | Main Current →Time  |  |  |
| 3. Peak off-state voltage $V_D = 400 \text{ V}$                          | Main Voltage → Time<br>(dv/dt)c V <sub>D</sub>                |  |  |

### **Performance Curves**



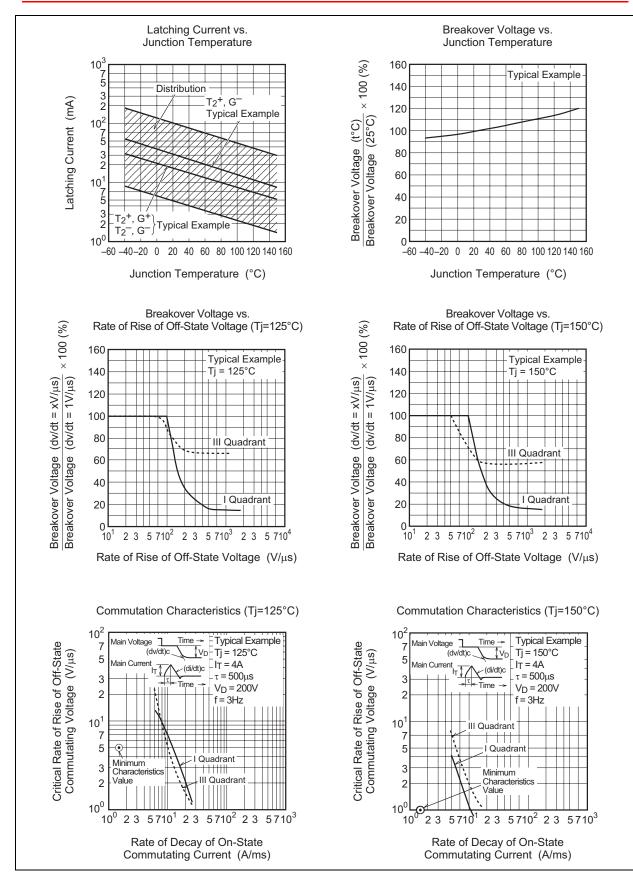
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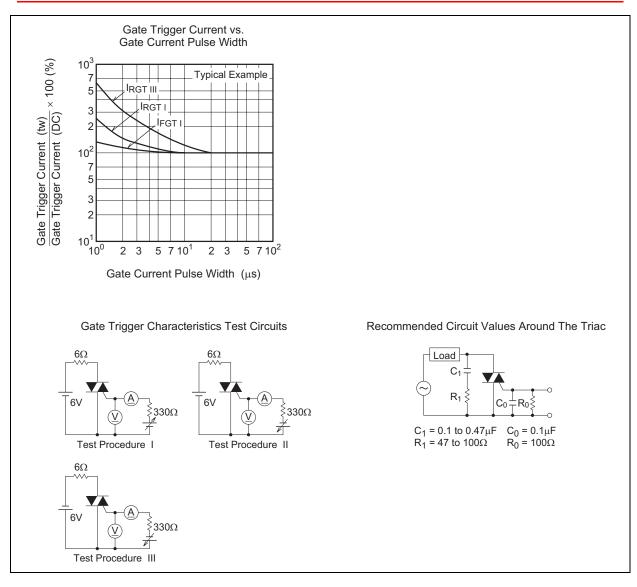
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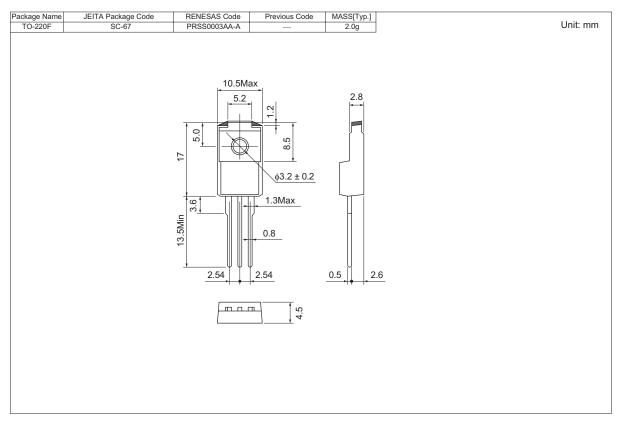
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# **Package Dimensions**



### Order Code

| Lead form     | Standard packing        | Quantity | Standard order code           | Standard order<br>code example |
|---------------|-------------------------|----------|-------------------------------|--------------------------------|
| Straight type | Vinyl sack              | 100      | Type name                     | BCR3PM-14LG                    |
| Lead form     | Plastic Magazine (Tube) | 50       | Type name – Lead forming code | BCR3PM-14LG-A8                 |

Note : Please confirm the specification about the shipping in detail.

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http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

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